# Instructions for drawing up the abstract of the II International Scientific and Technical Conference “OPTO-, MICRO- AND MICROWAVE – ELECTRONICS – 2022”

## I. I. Ivanov a), P. P. Petrov b), S. S. Sidorov c)

### а) Name of organization 1, City 1, Country 1 b) Name of organization 2, City 2, Country 2; e-mail: [p.petrov@e-pochta.ru](mailto:p.petrov@e-pochta.ru) c) Name of organization 3, City 3, Country 3

The language of the abstract should Russian or English. The volume of the abstract should not exceed 1 page. The abstract should be prepared in strict accordance with the instructions presented in this template with the MS Word text editor.

The abstract should be typed with a single interval using the Times New Roman font of 12 size on a standard A4 sheet with fields of 20 mm from above, below, left and right. The abstract title should be located in the center at the top of the page and should be scored by the bold font of the lower register with the capital letters only of the names of its own and acronyms. Use the symbols of the upper index (letters) to link the names of the authors with the relevant organizations that should be scored in the center right after the names of the authors. The surname of the author-speaker should be underlined, and his (her) email should be indicated after the address of the organization, which he (she) represents.

It is allowed to place only one figure in the abstract, which is not numbered, and its signature should be in the form “Fig. Figure caption”. The figure should be clear and finished high-quality illustrative material. Labels on the figure should be have the font size, which is sufficient for easy reading.

References should be numbered in the mention in the text, place their numbers in square brackets, for example, [1, 3–5, 7]. References are given after 1 interval after the abstract text and typed using the Times New Roman font 10 size. Samples of references [1–5] are given below. All authors must be listed for references.

1. Chuang S. L. Efficient band-structure calculations of strained quantum wells. Phys. Rev. B. 1991. Vol. 43, No. 12. P. 9649–9661.
2. Li Z.-M., Bradford T. A comparative study of temperature sensitivity of InGaAsP and AlGaAs MQW lasers. IEEE J. Quantum Electron. 1995. Vol. 31, No. 10. P. 1841–1847.
3. Agrawal G. P., Dutta N. K. Long-Wavelength Semiconductor Lasers. N. Y., 1986.
4. Smith R. G., Personick S. D. Basic design of optical fiber communications systems. Semiconductor Device for Optical Communication. Vol. 1. Eds. H. Kressel and G. H. Locwood. San Francisco, 1980. P. 121–135.
5. Jaworski M. Optical modulation formats for high-speed DWDM systems. Proc. 5th Int. Conf. on Transparent Optical Networks. Vol. 2. Warsaw, 2003. P. 162–165.